

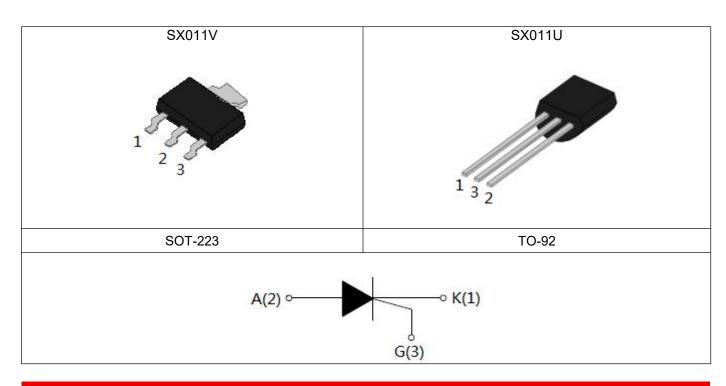




SX011 Series Sensitive gate SCRs

Description

The SX011 SCR series provide high dv/dt rate with strong resistance to electromagnetic interface. They are especially recommended for use on residual current circuit breaker, straight hair, igniter etc.



Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Storage junction temperature range	TJ	-	-40 to +110	°C
Operating junction temperature range	T _{stg}	-	-40 to +150	°C
Repetitive peak off-state voltage	V_{DRM}	-	800	V
Repetitive peak reverse voltage	V_{RRM}	-	800	V
RMS on-state current	I _(TRMS)	TO-92(T _C =65°C)	4	Δ.
		SOT-223(T _C =75°C)	1	Α
Non repetitive surge peak on-state current(tp=10ms)	I _{TSM}	-	12	А
I2t value for fusing (tp=10ms)	l²t	-	0.72	A ² s
Critical rate of rise of on-state current	dl/dt	-	50	A/us
Peak gate current (tp=20 µ s, Tj=110℃)	I _{GM}	-	0.3	А
Peak gate power (tp=20 µ s, Tj=110℃)	P _{GM}	-	0.5	W
Average gate power dissipation(Tj=110℃)	P _{G(AV)}	-	0.1	W

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Electrical Characteristics(Tj=25℃ unless otherwise specified)

Symbol	Condition	Min.	Тур.	Max.	Units
I _{GT}	V =12V D =22O	-	40	200	μA
V_{GT}	V _D =12V R _L =33Ω	-	0.6	0.8	V
V_{GD}	$V_D = V_{DRM} T_j = 110^{\circ}C$	0.2	-	-	V
lι	I _G =1.2 I _{GT}	-	-	5	mA
l _H	I _T =0.05A	-	-	4	mA
dV/dt	$V_D=2/3V_{DRM} T_j=110^{\circ}C R_{GK}=1K\Omega$	100	200	-	V/µs

^{*} Pulse width < 300 µs, duty cycle < 2%

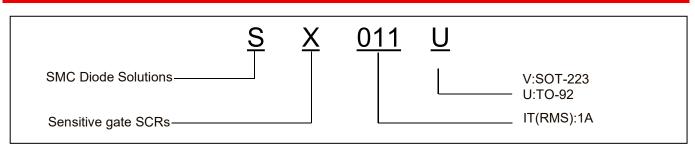
Static Characteristics

Symbol	Condition	Max.	Units
V_{TM}	I _T =2A tp=380μs,Tj=25℃	1.7	V
I _{DRM}	V _D =V _{DRM} V _R =V _{RRM} , Tj=25°C	5	uA
I _{RRM}	$V_D = V_{DRM} V_R = V_{RRM}, Tj = 110^{\circ}C$	100	uA

Thermal Resistances

Symbol	Condition		Value	Units	
Rth(j-c)	Junction to case	TO-92	70	°C/W	
		SOT-223	25		

Ordering Information



Device	Package	Shipping
SX011V	SOT-223	4000pcs/ reel
SX011VTR	SOT-223	4000pcs/ reel
SX011U	TO-92	1000pcs/ bag

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Ratings and Characteristics Curves

FIG.1: Maximum power dissipation versus RMS on-state current

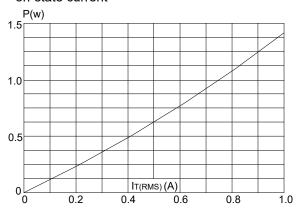


FIG.3: Surge peak on-state current versus number of cycles

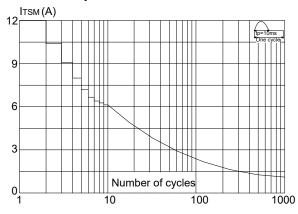


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<10ms ($dI/dt \le 50A/\mu s$)

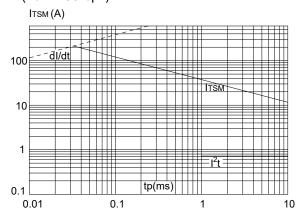


FIG.2: RMS on-state current versus case temperature

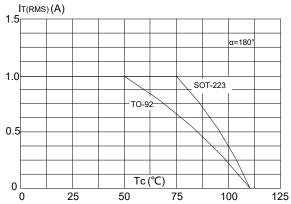


FIG.4: On-state characteristics (maximum values)

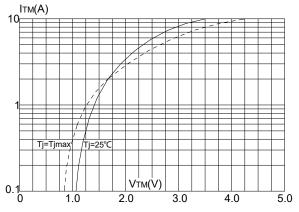
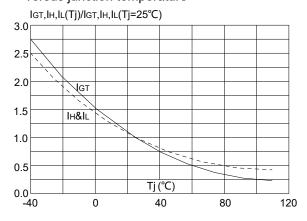


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



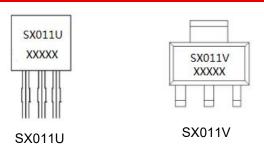
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Marking Diagram



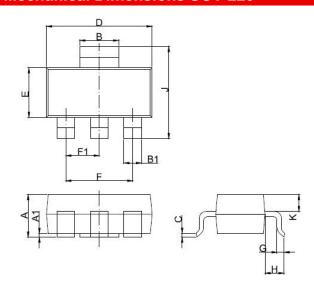
Where XXXXX is YYWWL

= SMC

= Sensitive gate SCRs = Forward Current (1A) 011 V/U = Package type ΥY = Year ww = Week

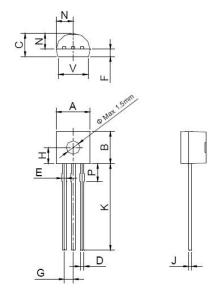
= Lot Number

Mechanical Dimensions SOT-223



SYMBO	Millimeters			Inches		
L	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	1.5	1.6	1.8	0.059	0.063	0.071
A1	0.01	0.06	0.10	0.001	0.002	0.004
В	2.9	3.0	3.1	0.114	0.118	0.122
B1	0.6	0.7	0.8	0.024	0.028	0.031
С	0.22	0.26	0.32	0.009	0.010	0.013
D	6.3	6.5	6.7	0.248	0.256	0.264
Е	3.3	3.5	3.7	0.130	0.138	0.146
F		4.6			0.181	
F1		2.3			0.091	
G	0.7	0.9	1.1	0.028	0.035	0.043
Н	1.50	1.5	2.0	0.059	0.069	0.079
J	6.7	7.0	7.3	0.264	0.276	0.287
K	0.8	0.9	1.0	0.031	0.035	0.039

Mechanical Dimensions TO-92



SYMBO	Millimeters			Inches		
L	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	4.45	-	5.20	0.175	-	0.205
В	4.32	-	5.33	0.170	-	0.210
С	3.18	-	4.19	0.125	-	0.165
D	0.407	-	0.533	0.016	-	0.021
E	0.50	-	0.70	0.020	-	0.028
F	1.10	-	1.30	-		0.051
G	1.10	-	1.40	0.043		0.055
Н	2.20	-	2.40	0.087		0.094
J	0.36	-	0.50	0.014	-	0.020
K	12.70	1	15.0	0.500	•	0.591
N	2.04	-	2.66	0.080	-	0.105
Р	1.80	-	2.30	0.071	-	0.091
V	4.10	-	4.50	0.161	-	0.177

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